

Line Number	Hits	Search Text	LP	Time Stamp
1	170	high near (dielectric insulat\$3; near constant).ti.	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:33
2	184	high near (dielectric insulat\$3; near constant .ti.) and (gap cavity groove opening recess trench)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:36
3	150	((high near (dielectric insulat\$3; near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:46
4	122	((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)) and @ad<20000526	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 09:54
5	94	(((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)) and @ad<20000526) and capacitor	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:10
6	25	(((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)) and @ad<20000526) and capacitor) and conductor	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:10
7	43095	high near (dielectric insulat\$3 K)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:34
8	16877	(high near (dielectric insulat\$3 K) and (gap cavity groove opening recess trench)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:41
9	1656	((high near (dielectric insulat\$3 K) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer))	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:45
10	1624	((high near (dielectric insulat\$3 K) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer))) and (metal wir\$3 conduct\$3)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:47
11	995	((high near (dielectric insulat\$3 K) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer)) and (metal wir\$3 conduct\$3)) and capacitor	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:47
12	954	((high near (dielectric insulat\$3 K) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer))) and (metal wir\$3 conduct\$3)) and capacitor) and (substrate wafer pad base)	USPAT; US-PGPUB; EPO; JPO; DEPWENT; IBM_TDB	2003/01/21 10:48